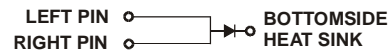
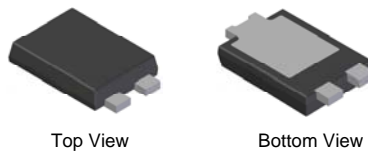


## Features

- Designed as Bypass Diodes for Solar Panels
- Selectively Rated for 200°C Maximum Junction Temperature for High Thermal Reliability
- Patented Super Barrier Rectifier Technology
- High Forward Surge Capability
- Ultra Low Forward Voltage Drop
- Excellent High Temperature Stability
- **Lead Free Finish, RoHS Compliant (Note 2)**

## Mechanical Data

- Case: PowerDI<sup>®</sup>5
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.093 grams (approximate)



Note: Pins Left & Right must be electrically connected at the printed circuit board.

## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.  
For capacitance load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	45	V
Working Peak Reverse Voltage	V <sub>RWM</sub>		
DC Blocking Voltage	V <sub>RM</sub>		
RMS Reverse Voltage	V <sub>R(RMS)</sub>	32	V
Average Rectified Output Current	I <sub>O</sub>	10	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I <sub>FSM</sub>	275	A

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance			
Thermal Resistance Junction to Ambient (Note 3)	R <sub>θJA</sub>	73	°C/W
Thermal Resistance Junction to Ambient (Note 4)	R <sub>θJA</sub>	31	
Operating Temperature Range	T <sub>J</sub>	V <sub>R</sub> ≤ 80% V <sub>RRM</sub>	-65 to +150
		V <sub>R</sub> ≤ 50% V <sub>RRM</sub>	≤180
		DC Forward Mode	≤200
Storage Temperature Range	T <sub>STG</sub>	-65 to +175	°C

## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 1)	V <sub>(BR)R</sub>	45	-	-	V	I <sub>R</sub> = 0.3mA
Forward Voltage Drop	V <sub>F</sub>	-	-	0.42	V	I <sub>F</sub> = 8A, T <sub>J</sub> = 25°C
		-	0.42	0.47		I <sub>F</sub> = 10A, T <sub>J</sub> = 25°C
		-	0.38	0.41		I <sub>F</sub> = 10A, T <sub>J</sub> = 125°C
Leakage Current (Note 1)	I <sub>R</sub>	-	0.05	0.3	mA	V <sub>R</sub> = 45V, T <sub>J</sub> = 25°C
		-	-	15		V <sub>R</sub> = 45V, T <sub>J</sub> = 100°C
		-	28.0	75		V <sub>R</sub> = 45V, T <sub>J</sub> = 150°C

- Notes:
1. Short duration pulse test used to minimize self-heating effect.
  2. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied, see *EU Directive 2002/95/EC Annex Notes*.
  3. FR-4 PCB, 2oz. Copper, minimum recommended pad layout per <http://www.diodes.com/datasheets/ap02001.pdf>.
  4. Polyimide PCB, 2oz. Copper. Cathode pad dimensions 18.8mm x 14.4mm. Anode pad dimensions 5.6mm x 14.4mm.

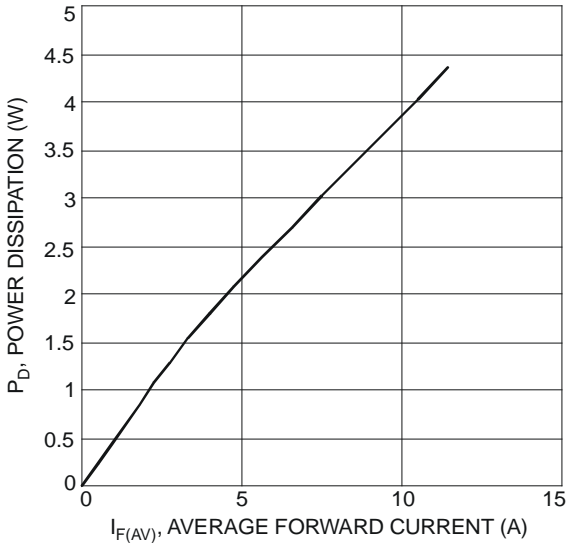


Fig. 1 Forward Power Dissipation

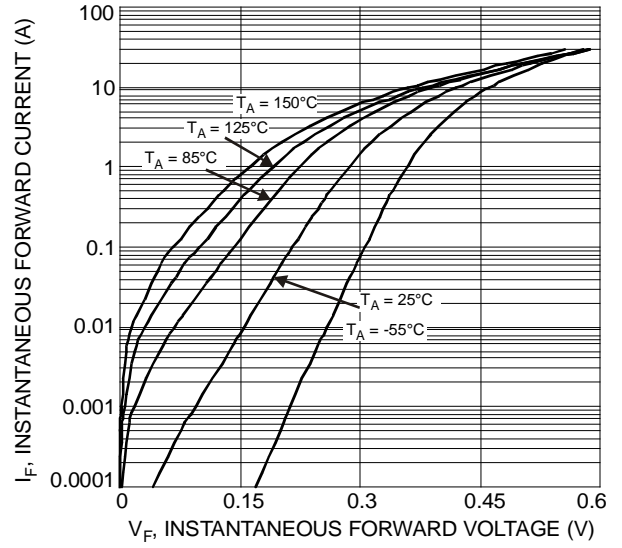


Fig. 2 Typical Forward Characteristics

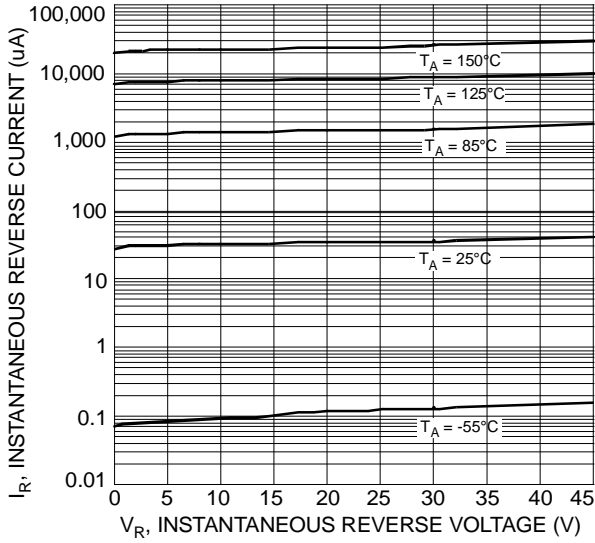


Fig. 3 Typical Reverse Characteristics

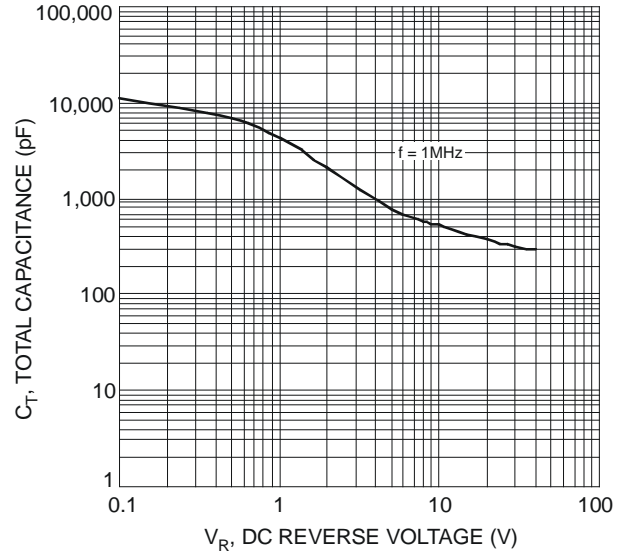


Fig. 4 Total Capacitance vs. Reverse Voltage

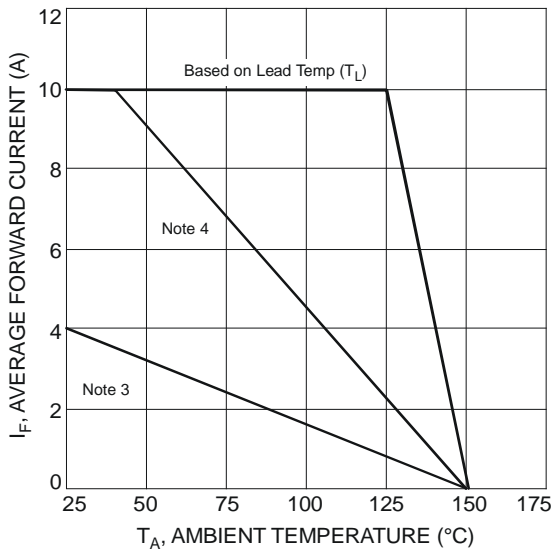


Fig. 5 Forward Current Derating Curve